NSN 5962-01-303-9931

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-303-9931

Overall Length:

0.308 inches

Overall Height:

0.100 inches

Overall Width:

0.308 inches

Body Length:

0.375 inches

Body Width:

0.375 inches

Body Height:

0.088 inches

Maximum Power Dissipation Rating:

1.1 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and burn in and monolithic and programmable

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

C-2 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes forward current, nonrepetitive, peak total value

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

12.0 volts power source

Memory Device Type:

Pal

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

20 leadless

NSN 5962-01-303-9931

Memory Microcircuit - Page 2 of 2



Specification Data:

81349-mil-m-38510/504 government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A458a0